

FX20ASJ-03F

High-Speed Switching Use Pch Power MOS FET

REJ03G0248-0100 Rev.1.00 Aug.20.2004

Features

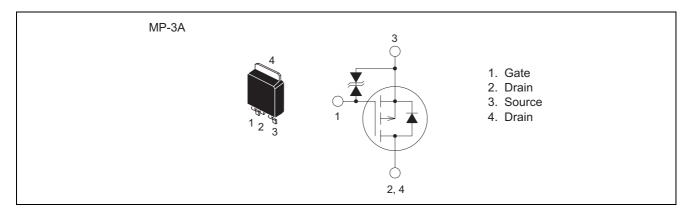
• Drive voltage: 4 V

• V_{DSS} : -30 V

• $r_{DS(ON) \, (max)}$: 0.12 Ω

• $I_D: -20 A$

Outline



Applications

Motor control, lamp control, solenoid control, DC-DC converters, etc.

Maximum Ratings

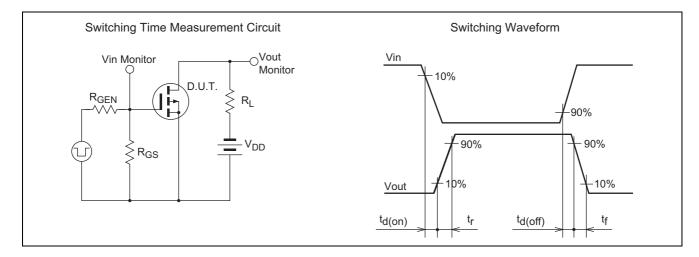
 $(Tc = 25^{\circ}C)$

Parameter Symbo		Ratings	Unit	Conditions	
Drain-source voltage	rain-source voltage V _{DSS}		V	V _{GS} = 0 V	
Gate-source voltage	e-source voltage V _{GSS}		V	$V_{DS} = 0 V$	
Drain current	I _D	-20	Α		
Drain current (Pulsed)	I _{DM}	- 40	Α		
Avalanche current (Pulsed)	I _{DA}	- 5	Α	L = 10 μH	
Source current	Is	-20	Α		
Source current (Pulsed)	I _{SM}	- 40	Α		
Maximum power dissipation	P _D	25	W		
Channel temperature	Tch	- 55 to +150	°C		
Storage temperature	Tstg	- 55 to +150	°C		
Mass	_	0.32	g	Typical value	

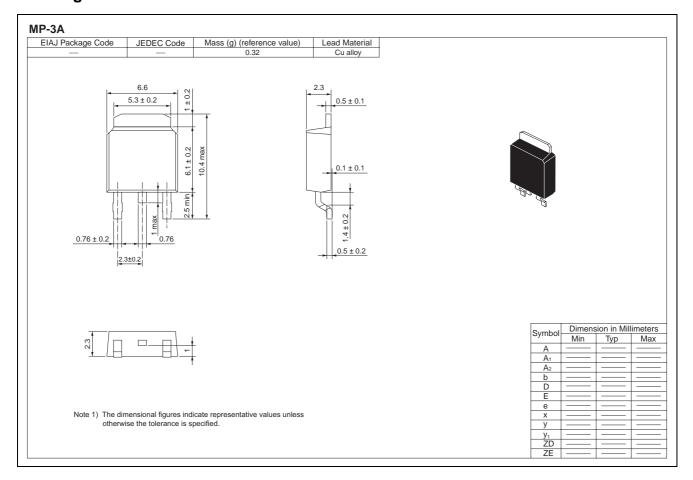
Electrical Characteristics

 $(Tch = 25^{\circ}C)$

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test conditions
Drain-source breakdown voltage	$V_{(BR)DSS}$	-30	_	_	V	$I_D = 1 \text{ mA}, V_{GS} = 0 \text{ V}$
Gate-source breakdown voltage	$V_{(BR)GSS}$	±20		_	>	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0 \ V$
Drain-source leakage current	I _{DSS}		_	100	μΑ	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$
Gate-source leakage current	I _{GSS}		_	±10	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$
Gate-source threshold voltage	$V_{GS(th)}$	-1.5	-2.0	-2.5	V	$I_D = -1 \text{ mA}, V_{DS} = -10 \text{ V}$
Drain-source on-state resistance	r _{DS(ON)}		0.085	0.12	Ω	$I_D = -10 \text{ A}, V_{GS} = -10 \text{ V}$
Drain-source on-state resistance	r _{DS(ON)}		0.145	0.20	Ω	$I_D = -2 A$, $V_{GS} = -4 V$
Drain-source on-state voltage	V _{DS(ON)}		-0.85	-1.2	V	$I_D = -10 \text{ A}, V_{GS} = -10 \text{ V}$
Forward transfer admittance	y _{fs}		8	_	S	$I_D = -10 \text{ A}, V_{DS} = -5 \text{ V}$
Input capacitance	Ciss		500	_	pF	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V},$
Output capacitance	Coss	1	100	_	pF	f = 1MHz
Reverse transfer capacitance	Crss	1	80	_	pF	
Turn-on delay time	t _{d(on)}		6	_	ns	$V_{DD} = -15 \text{ V}, I_D = -10 \text{ A},$
Rise time	t _r		8	_	ns	$V_{GS} = -10 \text{ V},$
Turn-off delay time	t _{d(off)}		40	_	ns	$R_{GEN} = R_{GS} = 50 \Omega$
Fall time	t _f		15	_	ns	
Source-drain voltage	V _{SD}		-1.0	-1.5	V	$I_S = -10 \text{ A}, V_{GS} = 0 \text{ V}$
Thermal resistance	Rth(ch-c)		_	5.0	°C/W	Channel to case
Reverse recovery time	t _{rr}	_	30	_	ns	$I_S = -10 \text{ A}, \text{ dis/dt} = -50 \text{ A/}\mu\text{s}$



Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Surface-mounted type Taping		3000	Type name – T +Direction (1 or 2) +3	FX20ASJ-03F-T13
Surface-mounted type	face-mounted type Plastic Magazine 75 (Tube)		Type name	FX20ASJ-03F

Note: Please confirm the specification about the shipping in detail.

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